Please cancel claim 21 without prejudice.

21. (Currently cancelled) ~~A method of making a semiconductor device comprising:~~

~~providing a substrate 101,114 having a surface and a diffused region of a second conductivity type PHV 114 for forming a channel 115 of the semiconductor device;~~

~~forming a drain 106,107,110,113 of a first conductivity type at the surface for electrically coupling a drain electrode to the channel;~~

~~growing an oxide 103 less than one thousand angstroms thick over the drain; and~~

~~introducing dopants of a second conductivity type through the oxide between the channel and the drain electrode to form a first charge balancing layer108 within the drain and at the surface.~~

22. (Currently amended) ~~The method of claim 21,~~ A method of making a semiconductor device comprising:

providing a substrate 101,114 having a surface and a diffused region of a second conductivity type PHV 114 for forming a channel 115 of the semiconductor device;

forming a drain 106,107,110,113 of a first conductivity type at the surface for electrically coupling a drain electrode to the channel; wherein the step of forming a drain further comprises~~:~~

forming a first area 110 of first dopant concentration by performing a first area implant~~505;~~, and

forming a second area 112 of second dopant concentration different than the first dopant concentration by performing a second area implant 507, the second area implant is laterally offset from the first area;

growing an oxide 103 less than one-thousand angstroms thick over the drain; and

introducing dopants of a second conductivity type through the oxide between the channel and the drain electrode to form a first charge balancing layer108 within the drain and at the surface.

23. (Currently Amended) The method of claim 2~~1~~2, further comprising introducing dopants of the second conductivity type through the oxide to form a second charge balancing layer_ 302 within the drain and under the first charge balancing layer.

24. (Previously Added) The method of claim 23, further comprising forming a gate region 105 overlying the oxide.

25. (Currently Amended) The method of claim 2~~1~~2, further comprising forming a diffused region 114 of the first conductivity type.

26. (Previously Added) The method of claim 25, further comprising forming a source diffusion region 102 in the diffused region of the first conductivity type.

27. (Currently Amended) The method of claim 24~~2~~, further comprising forming a drain diffusion region 106 at the surface of the drain.

28. (Currently Amended) The method of claim 24~~2~~, wherein introducing dopants includes the step of:

disposing a first island of dielectric material (126)at a top of the substrate within the drain; and

disposing a second island of dielectric material (126)at a top of the substrate within the drain and laterally separated from the first island of dielectric material; and

masking the dopants with the first and second islands to form the first charge balancing layer between the first and second islands of dielectric material.

29. (Previously Added) The method of claim 28, wherein the first and second islands of dielectric material are formed to a thickness of greater than one micrometer.